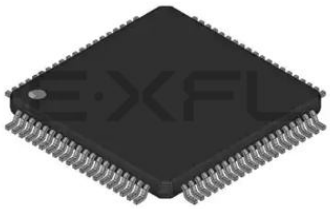
Infineon Technologies - XC2336A56F80LAAFXUMA1 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16/32-Bit
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	40
Program Memory Size	448KB (448K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	50K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	PG-LQFP-64-13
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xc2336a56f80laafxuma1

1.2 Special Device Types

Special device types are only available for high-volume applications on request.

Table 2 Synopsis of XC233xA Special Device Types

Derivative[1)]	Flash Memory[2)]	PSRAM DSRAM[3)]	Capt./Comp. Modules	ADC[4)] Chan.	Interfaces[4)]
XC2336A-72FxxL	576 Kbytes	32 Kbytes 16 Kbytes	CC2 CCU60/1	7 + 2	2 CAN Nodes, 4 Serial Chan.
XC2336A-56FxxL	448 Kbytes	16 Kbytes 16 Kbytes	CC2 CCU60/1	7 + 2	2 CAN Nodes, 4 Serial Chan.

1) xx is a placeholder for the available speed grade (in MHz).

2) Specific information about the on-chip Flash memory in **Table 3**.

3) All derivatives additionally provide 8 Kbytes SBRAM and 2 Kbytes DPRAM.

4) Specific information about the available channels in **Table 5**.
Analog input channels are listed for each Analog/Digital Converter module separately (ADC0 + ADC1).

Table 6 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
20	P5.8	I	In/A	**Bit 8 of Port 5, General Purpose Input**
	ADC0_CH8	I	In/A	**Analog Input Channel 8 for ADC0**
	ADC1_CH8	I	In/A	**Analog Input Channel 8 for ADC1**
	CCU6x_T12HRC	I	In/A	**External Run Control Input for T12 of CCU60/1**
	CCU6x_T13HRC	I	In/A	**External Run Control Input for T13 of CCU60/1**
21	P5.10	I	In/A	**Bit 10 of Port 5, General Purpose Input**
	ADC0_CH10	I	In/A	**Analog Input Channel 10 for ADC0**
	ADC1_CH10	I	In/A	**Analog Input Channel 10 for ADC1**
	$\overline{\text{BRKIN\_A}}$	I	In/A	**OCDS Break Signal Input**
	CCU61_T13HRA	I	In/A	**External Run Control Input for T13 of CCU61**
22	P5.13	I	In/A	**Bit 13 of Port 5, General Purpose Input**
	ADC0_CH13	I	In/A	**Analog Input Channel 13 for ADC0**
23	P5.15	I	In/A	**Bit 15 of Port 5, General Purpose Input**
	ADC0_CH15	I	In/A	**Analog Input Channel 15 for ADC0**
25	P2.0	O0 / I	St/B	**Bit 0 of Port 2, General Purpose Input/Output**
	RxDC0C	I	St/B	**CAN Node 0 Receive Data Input**
	T5INB	I	St/B	**GPT12E Timer T5 Count/Gate Input**
26	P2.1	O0 / I	St/B	**Bit 1 of Port 2, General Purpose Input/Output**
	TxDC0	O1	St/B	**CAN Node 0 Transmit Data Output**
	T5EUDB	I	St/B	**GPT12E Timer T5 External Up/Down Control Input**
	ESR1_5	I	St/B	**ESR1 Trigger Input 5**
27	P2.2	O0 / I	St/B	**Bit 2 of Port 2, General Purpose Input/Output**
	TxDC1	O1	St/B	**CAN Node 1 Transmit Data Output**
	ESR2_5	I	St/B	**ESR2 Trigger Input 5**

2.2 Identification Registers

The identification registers describe the current version of the XC233xA and of its modules.

Table 7 XC233xA Identification Registers

Short Name	Value	Address	Notes
SCU_IDMANUF	1820_H	$00'F07E_H$	
SCU_IDCHIP	3801_H	$00'F07C_H$	
SCU_IDMEM	$30D0_H$	$00'F07A_H$	
SCU_IDPROG	1313_H	$00'F078_H$	
JTAG_ID	$0017'E083_H$	---	marking EES-AA, ES-AA or AA

8 Kbytes of on-chip Stand-By SRAM (SBRAM) provide storage for system-relevant user data that must be preserved while the major part of the device is powered down. The SBRAM is accessed via a specific interface and is powered in domain M.

1024 bytes (2 × 512 bytes) of the address space are reserved for the Special Function Register areas (SFR space and ESFR space). SFRs are word-wide registers which are used to control and monitor functions of the different on-chip units. Unused SFR addresses are reserved for future members of the XC2000 Family. In order to ensure upward compatibility they should either not be accessed or written with zeros.

The on-chip Flash memory stores code, constant data, and control data. The on-chip Flash memory consists of 1 module of 64 Kbytes (preferably for data storage) and modules with a maximum capacity of 256 Kbytes each. Each module is organized in sectors of 4 Kbytes.
The uppermost 4-Kbyte sector of segment 0 (located in Flash module 0) is used internally to store operation control parameters and protection information.

Note: The actual size of the Flash memory depends on the chosen device type.

Each sector can be separately write protected[1)], erased and programmed (in blocks of 128 Bytes). The complete Flash area can be read-protected. A user-defined password sequence temporarily unlocks protected areas. The Flash modules combine 128-bit read access with protected and efficient writing algorithms for programming and erasing. Dynamic error correction provides extremely high read data security for all read access operations. Access to different Flash modules can be executed in parallel.
For Flash parameters, please see **Section 4.5**.

Memory Content Protection

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).
The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.
The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.

1) To save control bits, sectors are clustered for protection purposes, they remain separate for programming/erasing.

With this hardware most XC233xA instructions are executed in a single machine cycle of 12.5 ns with an 80-MHz CPU clock. For example, shift and rotate instructions are always processed during one machine cycle, no matter how many bits are shifted. Also, multiplication and most MAC instructions execute in one cycle. All multiple-cycle instructions have been optimized so that they can be executed very fast; for example, a 32-/16-bit division is started within 4 cycles while the remaining cycles are executed in the background. Another pipeline optimization, the branch target prediction, eliminates the execution time of branch instructions if the prediction was correct.

The CPU has a register context consisting of up to three register banks with 16 word-wide GPRs each at its disposal. One of these register banks is physically allocated within the on-chip DPRAM area. A Context Pointer (CP) register determines the base address of the active register bank accessed by the CPU at any time. The number of these register bank copies is only restricted by the available internal RAM space. For easy parameter passing, a register bank may overlap others.

A system stack of up to 32 Kwords is provided for storage of temporary data. The system stack can be allocated to any location within the address space (preferably in the on-chip RAM area); it is accessed by the CPU with the stack pointer (SP) register. Two separate SFRs, STKOV and STKUN, are implicitly compared with the stack pointer value during each stack access to detect stack overflow or underflow.

The high performance of the CPU hardware implementation can be best utilized by the programmer with the highly efficient XC233xA instruction set. This includes the following instruction classes:

- Standard Arithmetic Instructions
- DSP-Oriented Arithmetic Instructions
- Logical Instructions
- Boolean Bit Manipulation Instructions
- Compare and Loop Control Instructions
- Shift and Rotate Instructions
- Prioritize Instruction
- Data Movement Instructions
- System Stack Instructions
- Jump and Call Instructions
- Return Instructions
- System Control Instructions
- Miscellaneous Instructions

The basic instruction length is either 2 or 4 bytes. Possible operand types are bits, bytes and words. A variety of direct, indirect or immediate addressing modes are provided to specify the required operands.

3.7 Capture/Compare Unit (CAPCOM2)

The CAPCOM2 unit supports generation and control of timing sequences on up to 16 channels with a maximum resolution of one system clock cycle (eight cycles in staggered mode). The CAPCOM2 unit is typically used to handle high-speed I/O tasks such as pulse and waveform generation, pulse width modulation (PWM), digital to analog (D/A) conversion, software timing, or time recording with respect to external events.

Two 16-bit timers (T7/T8) with reload registers provide two independent time bases for the capture/compare register array.

The input clock for the timers is programmable to several prescaled values of the internal system clock, or may be derived from an overflow/underflow of timer T6 in module GPT2. This provides a wide range or variation for the timer period and resolution and allows precise adjustments to the application-specific requirements. In addition, an external count input allows event scheduling for the capture/compare registers relative to external events.

The capture/compare register array contains 16 dual purpose capture/compare registers, each of which may be individually allocated to either CAPCOM timer and programmed for capture or compare function.
All registers have each one port pin associated with it which serves as an input pin for triggering the capture function, or as an output pin to indicate the occurrence of a compare event.

When a capture/compare register has been selected for capture mode, the current contents of the allocated timer will be latched (‘captured’) into the capture/compare register in response to an external event at the port pin which is associated with this register. In addition, a specific interrupt request for this capture/compare register is generated. Either a positive, a negative, or both a positive and a negative external signal transition at the pin can be selected as the triggering event.

The contents of all registers which have been selected for one of the five compare modes are continuously compared with the contents of the allocated timers.

When a match occurs between the timer value and the value in a capture/compare register, specific actions will be taken based on the selected compare mode.

Table 9 Compare Modes

Compare Modes	Function
Mode 0	Interrupt-only compare mode; Several compare interrupts per timer period are possible
Mode 1	Pin toggles on each compare match; Several compare events per timer period are possible

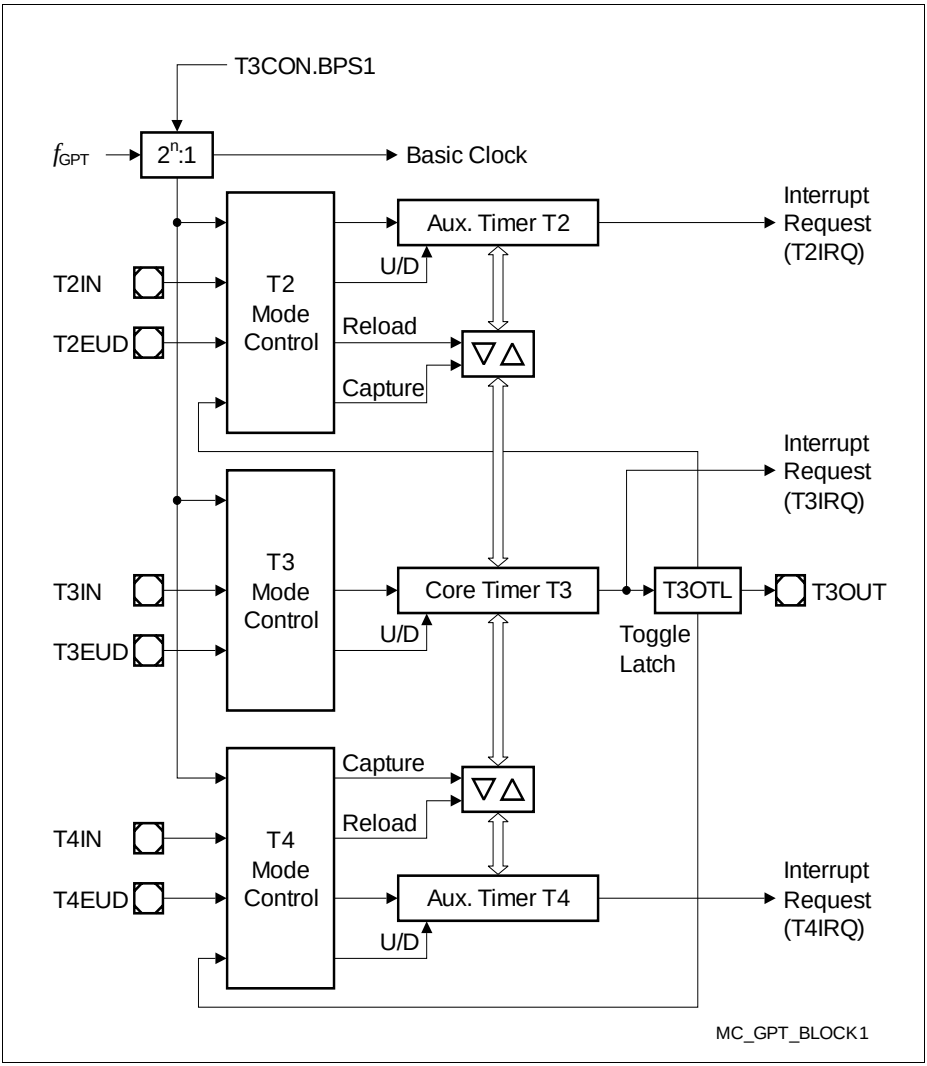

Figure 8 Block Diagram of GPT1

3.13 MultiCAN Module

The MultiCAN module contains independently operating CAN nodes with Full-CAN functionality which are able to exchange Data and Remote Frames using a gateway function. Transmission and reception of CAN frames is handled in accordance with CAN specification V2.0 B (active). Each CAN node can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers.

All CAN nodes share a common set of message objects. Each message object can be individually allocated to one of the CAN nodes. Besides serving as a storage container for incoming and outgoing frames, message objects can be combined to build gateways between the CAN nodes or to set up a FIFO buffer.

Note: The number of CAN nodes and message objects depends on the selected device type.

The message objects are organized in double-chained linked lists, where each CAN node has its own list of message objects. A CAN node stores frames only into message objects that are allocated to its own message object list and it transmits only messages belonging to this message object list. A powerful, command-driven list controller performs all message object list operations.

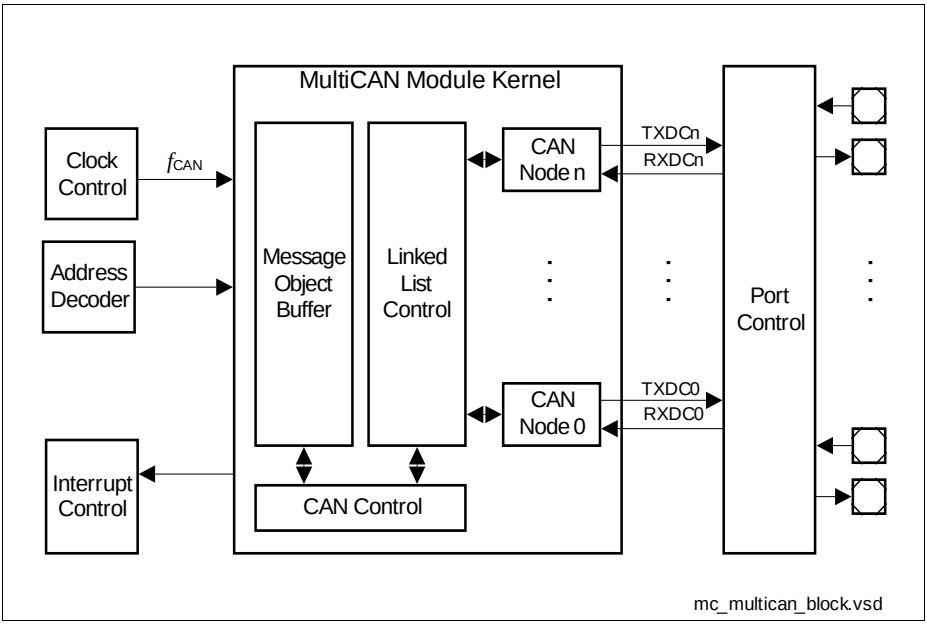

Figure 12 Block Diagram of MultiCAN Module

3.17 Parallel Ports

The XC233xA provides up to 40 I/O lines which are organized into 4 input/output ports and 2 input ports. All port lines are bit-addressable, and all input/output lines can be individually (bit-wise) configured via port control registers. This configuration selects the direction (input/output), push/pull or open-drain operation, activation of pull devices, and edge characteristics (shape) and driver characteristics (output current) of the port drivers. The I/O ports are true bidirectional ports which are switched to high impedance state when configured as inputs. During the internal reset, all port pins are configured as inputs without pull devices active.

All port lines have alternate input or output functions associated with them. These alternate functions can be programmed to be assigned to various port pins to support the best utilization for a given application. For this reason, certain functions appear several times in **Table 10**.

All port lines that are not used for alternate functions may be used as general purpose I/O lines.

Table 10 Summary of the XC233xA's Ports

Port	Width	I/O	Connected Modules
P2	11	I/O	CAN, CC2, GPT12E, USIC, DAP/JTAG
P5	7	I	Analog Inputs, CCU6, DAP/JTAG, GPT12E, CAN
P6	2	I/O	ADC, CAN, GPT12E
P7	1	I/O	CAN, GPT12E, SCU, DAP/JTAG, USIC
P10	16	I/O	CCU6, USIC, DAP/JTAG, CAN
P15	2	I	Analog Inputs, GPT12E

4.1.2 Operating Conditions

The following operating conditions must not be exceeded to ensure correct operation of the XC233xA. All parameters specified in the following sections refer to these operating conditions, unless otherwise noticed.

Note: Typical parameter values refer to room temperature and nominal supply voltage, minimum/maximum parameter values also include conditions of minimum/maximum temperature and minimum/maximum supply voltage. Additional details are described where applicable.

Table 13 Operating Conditions

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Voltage Regulator Buffer Capacitance for DMP_M	C_{EVRM} SR	1.0	–	4.7	µF	1)
Voltage Regulator Buffer Capacitance for DMP_1	C_{EVR1} SR	0.47	–	2.2	µF	1)2)
External Load Capacitance	C_L SR	–	20[3)]	–	pF	pin out driver= default 4)
System frequency	f_{SYS} SR	–	–	100	MHz	5)
Overload current for analog inputs[6)]	I_{OVA} SR	-2	–	5	mA	not subject to production test
Overload current for digital inputs[6)]	I_{OVD} SR	-5	–	5	mA	not subject to production test
Overload current coupling factor for analog inputs[7)]	K_{OVA} CC	–	2.5×10^{-4}	1.5×10^{-3}	-	$I_{OV} < 0$ mA; not subject to production test
		–	1.0×10^{-6}	1.0×10^{-4}	-	$I_{OV} > 0$ mA; not subject to production test
Overload current coupling factor for digital I/O pins	K_{OVD} CC	–	1.0×10^{-2}	3.0×10^{-2}		$I_{OV} < 0$ mA; not subject to production test
		–	1.0×10^{-4}	5.0×10^{-3}		$I_{OV} > 0$ mA; not subject to production test

Table 14 DC Characteristics for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output Low Voltage[8]	V_{OL} CC	–	–	1.0	V	$I_{OL} \le I_{OLmax}$
		–	–	0.4	V	$I_{OL} \le I_{OLnom}$ [9]

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN} \le V_{ILmax}$ for a pullup; $V_{PIN} \ge V_{IHmin}$ for a pulldown.

6) These values apply to the fixed pull-devices in dedicated pins and to the user-selectable pull-devices in general purpose IO pins.

7) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} \ge V_{IHmin}$ for a pullup; $V_{PIN} \le V_{ILmax}$ for a pulldown.

8) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

9) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

Table 15 DC Characteristics for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output Low Voltage[8)]	V_{OL} CC	–	–	1.0	V	$I_{OL} \le I_{OLmax}$
		–	–	0.4	V	$I_{OL} \le I_{OLnom}$ [10)]

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN} <= V_{IL}$ for a pullup; $V_{PIN} >= V_{IH}$ for a pulldown.

6) These values apply to the fixed pull-devices in dedicated pins and to the user-selectable pull-devices in general purpose IO pins.

7) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} >= V_{IH}$ for a pullup; $V_{PIN} <= V_{IL}$ for a pulldown.

8) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

9) As a rule, with decreasing output current the output levels approach the respective supply level (VOL->VSS, VOH->VDDP). However, only the levels for nominal output currents are verified.

10) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

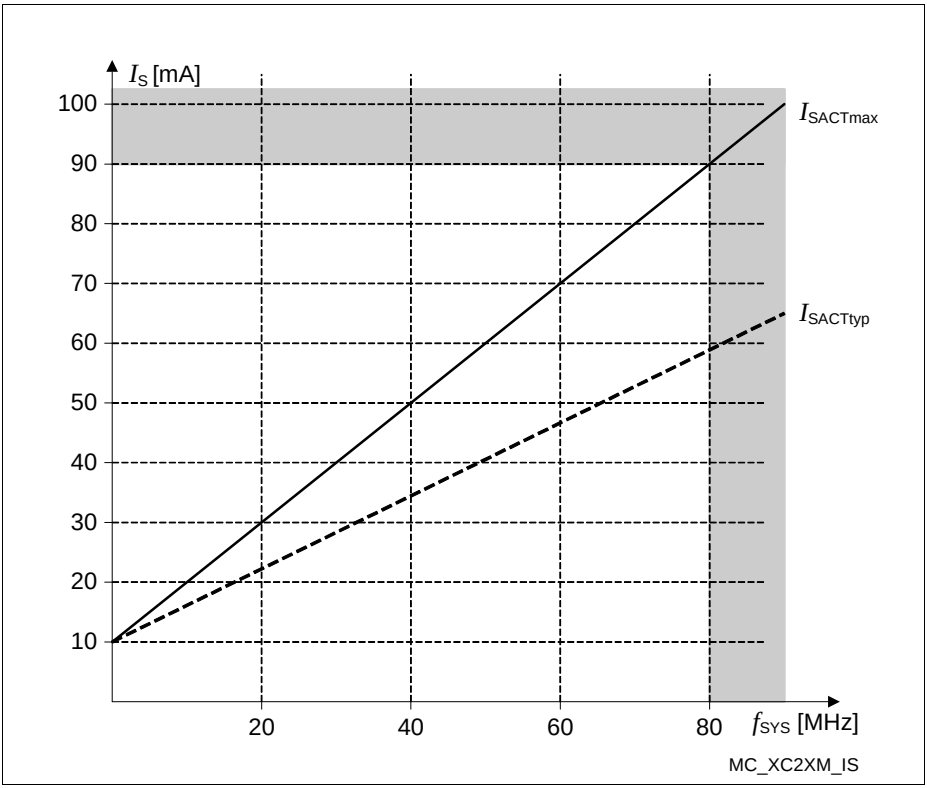

Figure 14 Supply Current in Active Mode as a Function of Frequency

Note: Operating Conditions apply.

Sample time and conversion time of the XC233xA's A/D converters are programmable. The timing above can be calculated using **Table 19**.
The limit values for f_{ADCI} must not be exceeded when selecting the prescaler value.

Table 19 A/D Converter Computation Table

GLOBCTR.5-0 (DIVA)	A/D Converter Analog Clock f_{ADCI}		INPCRx.7-0 (STC)	Sample Time[1] t_S
000000_B	f_{SYS}		00_H	$t_{ADCI} \times 2$
000001_B	f_{SYS} / 2		01_H	$t_{ADCI} \times 3$
000010_B	f_{SYS} / 3		02_H	$t_{ADCI} \times 4$
:	f_{SYS} / (DIVA+1)		:	$t_{ADCI} \times$ (STC+2)
111110_B	f_{SYS} / 63		FE_H	$t_{ADCI} \times 256$
111111_B	f_{SYS} / 64		FF_H	$t_{ADCI} \times 257$

1) The selected sample time is doubled if broken wire detection is active (due to the presampling phase).

Converter Timing Example A:

Assumptions: f_{SYS} = 80 MHz (i.e. t_{SYS} = 12.5 ns), DIVA = 03_H, STC = 00_H
Analog clock f_{ADCI} = f_{SYS} / 4 = 20 MHz, i.e. t_{ADCI} = 50 ns
Sample time t_S = $t_{ADCI} \times 2$ = 100 ns

Conversion 10-bit:

$t_{C10} = 13 \times t_{ADCI} + 2 \times t_{SYS} = 13 \times 50\text{ ns} + 2 \times 12.5\text{ ns} = 0.675\ \mu s$

Conversion 8-bit:

$t_{C8} = 11 \times t_{ADCI} + 2 \times t_{SYS} = 11 \times 50\text{ ns} + 2 \times 12.5\text{ ns} = 0.575\ \mu s$

Converter Timing Example B:

Assumptions: f_{SYS} = 40 MHz (i.e. t_{SYS} = 25 ns), DIVA = 02_H, STC = 03_H
Analog clock f_{ADCI} = f_{SYS} / 3 = 13.3 MHz, i.e. t_{ADCI} = 75 ns
Sample time t_S = $t_{ADCI} \times 5$ = 375 ns

Conversion 10-bit:

$t_{C10} = 16 \times t_{ADCI} + 2 \times t_{SYS} = 16 \times 75\text{ ns} + 2 \times 25\text{ ns} = 1.25\ \mu s$

Conversion 8-bit:

$t_{C8} = 14 \times t_{ADCI} + 2 \times t_{SYS} = 14 \times 75\text{ ns} + 2 \times 25\text{ ns} = 1.10\ \mu s$

4.5 Flash Memory Parameters

The XC233xA is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XC233xA's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 23 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	4[1)]		$N_{FL\_RD} \leq 1$, $f_{SYS} \leq 80$ MHz
		–	–	1[2)]		$N_{FL\_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq 20$ years
Flash wait states[3)]	$N_{WSFLASH}$ SR	1	–	–		$f_{SYS} \leq 8$ MHz
		2	–	–		$f_{SYS} \leq 13$ MHz
		3	–	–		$f_{SYS} \leq 17$ MHz
		4	–	–		$f_{SYS} > 17$ MHz
Erase time per sector/page	t_{ER} CC	–	7[4)]	8.0	ms	
Programming time per page	t_{PR} CC	–	3[4)]	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{Er} \leq 1\,000$ cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	

The timing in the AC Characteristics refers to TCSs. Timing must be calculated using the minimum TCS possible under the given circumstances.
The actual minimum value for TCS depends on the jitter of the PLL. Because the PLL is constantly adjusting its output frequency to correspond to the input frequency (from crystal or oscillator), the accumulated jitter is limited. This means that the relative deviation for periods of more than one TCS is lower than for a single TCS (see formulas and **Figure 20**).

This is especially important for bus cycles using waitstates and for the operation of timers, serial interfaces, etc. For all slower operations and longer periods (e.g. pulse train generation or measurement, lower baudrates, etc.) the deviation caused by the PLL jitter is negligible.

The value of the accumulated PLL jitter depends on the number of consecutive VCO output cycles within the respective timeframe. The VCO output clock is divided by the output prescaler K2 to generate the system clock signal f_{SYS}. The number of VCO cycles is K2 × **T**, where **T** is the number of consecutive f_{SYS} cycles (TCS).

The maximum accumulated jitter (long-term jitter) D_{Tmax} is defined by:

D_{Tmax} [ns] = $\pm(220 / (K2 \times f_{SYS}) + 4.3)$

This maximum value is applicable, if either the number of clock cycles T > (f_{SYS} / 1.2) or the prescaler value K2 > 17.

In all other cases for a timeframe of **T** × TCS the accumulated jitter D_T is determined by:

D_T [ns] = $D_{Tmax} \times [(1 - 0.058 \times K2) \times (T - 1) / (0.83 \times f_{SYS} - 1) + 0.058 \times K2]$

f_{SYS} in [MHz] in all formulas.

Example, for a period of 3 TCSs @ 33 MHz and K2 = 4:

$D_{max} = \pm(220 / (4 \times 33) + 4.3) = 5.97$ ns (Not applicable directly in this case!)

$D_3 = 5.97 \times [(1 - 0.058 \times 4) \times (3 - 1) / (0.83 \times 33 - 1) + 0.058 \times 4]$
$= 5.97 \times [0.768 \times 2 / 26.39 + 0.232]$
$= 1.7$ ns

Example, for a period of 3 TCSs @ 33 MHz and K2 = 2:

$D_{max} = \pm(220 / (2 \times 33) + 4.3) = 7.63$ ns (Not applicable directly in this case!)

$D_3 = 7.63 \times [(1 - 0.058 \times 2) \times (3 - 1) / (0.83 \times 33 - 1) + 0.058 \times 2]$
$= 7.63 \times [0.884 \times 2 / 26.39 + 0.116]$
$= 1.4$ ns

PLL frequency band selection

Different frequency bands can be selected for the VCO so that the operation of the PLL can be adjusted to a wide range of input and output frequencies:

Table 24 System PLL Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
VCO output frequency (VCO controlled)	f_{VCO} CC	50	–	110	MHz	VCOSEL = 00_B
		100	–	160	MHz	VCOSEL = 01_B
VCO output frequency (VCO free-running)	f_{VCO} CC	10	–	40	MHz	VCOSEL = 00_B
		20	–	80	MHz	VCOSEL = 01_B

4.6.2.2 Wakeup Clock

When wakeup operation is selected (SYSCON0.CLKSEL = 00_B), the system clock is derived from the low-frequency wakeup clock source:

$f_{SYS} = f_{WU}$.

In this mode, a basic functionality can be maintained without requiring an external clock source and while minimizing the power consumption.

4.6.2.3 Selecting and Changing the Operating Frequency

When selecting a clock source and the clock generation method, the required parameters must be carefully written to the respective bit fields, to avoid unintended intermediate states.

Many applications change the frequency of the system clock (f_{SYS}) during operation in order to optimize system performance and power consumption. Changing the operating frequency also changes the switching currents, which influences the power supply.

To ensure proper operation of the on-chip EVRs while they generate the core voltage, the operating frequency shall only be changed in certain steps. This prevents overshoots and undershoots of the supply voltage.

To avoid the indicated problems, recommended sequences are provided which ensure the intended operation of the clock system interacting with the power system.
Please refer to the Programmer's Guide.

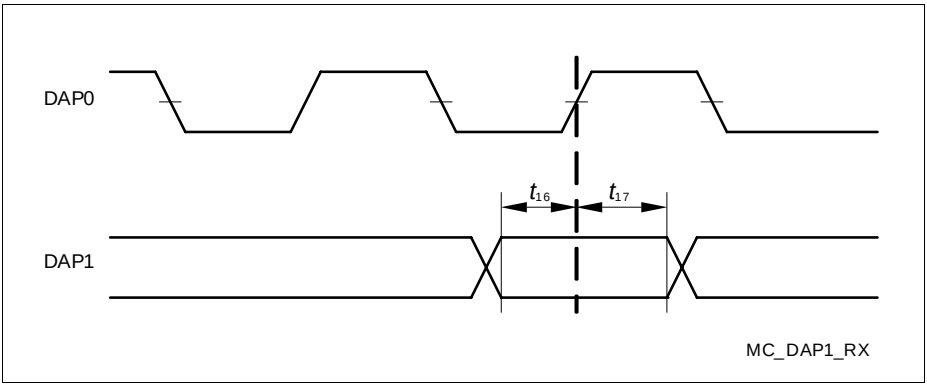

Figure 24 DAP Timing Host to Device

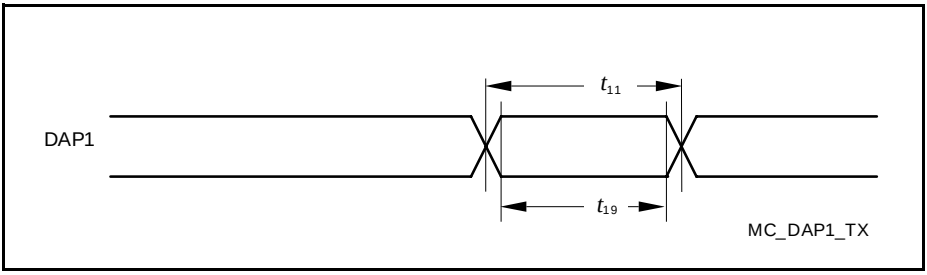

Figure 25 DAP Timing Device to Host

Note: The transmission timing is determined by the receiving debugger by evaluating the sync-request synchronization pattern telegram.

Debug via JTAG

The following parameters are applicable for communication through the JTAG debug interface. The JTAG module is fully compliant with IEEE1149.1-2000.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply; C_L= 20 pF.

Table 34 JTAG Interface Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50[1]	–	–	ns	[2]
TCK high time	t_2 SR	16	–	–	ns	
TCK low time	t_3 SR	16	–	–	ns	
TCK clock rise time	t_4 SR	–	–	8	ns	
TCK clock fall time	t_5 SR	–	–	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	–	–	ns	
TDI/TMS hold after TCK rising edge	t_7 SR	6	–	–	ns	
TDO valid from TCK falling edge (propagation delay)[3]	t_8 CC	–	25	29	ns	
TDO high impedance to valid output from TCK falling edge[4][3]	t_9 CC	–	25	29	ns	
TDO valid output to high impedance from TCK falling edge[3]	t_{10} CC	–	25	29	ns	
TDO hold after TCK falling edge[3]	t_{18} CC	5	–	–	ns	

1) The debug interface cannot operate faster than the overall system, therefore $t_1 \geq t_{SYS}$.

2) Under typical conditions, the interface can operate at transfer rates up to 20 MHz.

3) The falling edge on TCK is used to generate the TDO timing.

4) The setup time for TDO is given implicitly by the TCK cycle time.

Table 35 JTAG Interface Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50[1]	–	–	ns	[2]
TCK high time	t_2 SR	16	–	–	ns	
TCK low time	t_3 SR	16	–	–	ns	
TCK clock rise time	t_4 SR	–	–	8	ns	
TCK clock fall time	t_5 SR	–	–	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	–	–	ns	
TDI/TMS hold after TCK rising edge	t_7 SR	6	–	–	ns	
TDO valid from TCK falling edge (propagation delay)[3]	t_8 CC	–	32	36	ns	
TDO high impedance to valid output from TCK falling edge[4][3]	t_9 CC	–	32	36	ns	
TDO valid output to high impedance from TCK falling edge[3]	t_{10} CC	–	32	36	ns	
TDO hold after TCK falling edge[3]	t_{18} CC	5	–	–	ns	

1) The debug interface cannot operate faster than the overall system, therefore $t_1 \geq t_{SYS}$.

2) Under typical conditions, the interface can operate at transfer rates up to 20 MHz.

3) The falling edge on TCK is used to generate the TDO timing.

4) The setup time for TDO is given implicitly by the TCK cycle time.